

Power MOSFET



N-Channel MOSFET

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche, and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


 Available
RoHS*
 Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

APPLICABLE OFF LINE SMPS TOPOLOGIES

- Two transistor forward
- Half and full bridge
- Power factor correction boost

PRODUCT SUMMARY	
V_{DS} (V)	500
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V 0.52
Q_g max. (nC)	52
Q_{gs} (nC)	13
Q_{gd} (nC)	18
Configuration	Single

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free	IRFB11N50APbF
Lead (Pb)-free and halogen-free	IRFB11N50APbF-BE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	500	V
Gate-source voltage		V_{GS}	± 30	
Continuous drain current	V_{GS} at 10 V	I_D	$T_C = 25^\circ\text{C}$	11
			$T_C = 100^\circ\text{C}$	7.0
Pulsed drain current ^a		I_{DM}	44	A
Linear derating factor			1.3	W/ $^\circ\text{C}$
Single pulse avalanche energy ^b		E_{AS}	275	mJ
Repetitive avalanche current ^a		I_{AR}	11	A
Repetitive avalanche energy ^a		E_{AR}	17	mJ
Maximum power dissipation	$T_C = 25^\circ\text{C}$	P_D	170	W
Peak diode recovery dV/dt ^c		dV/dt	6.9	V/ns
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Soldering recommendations (peak temperature) ^d	For 10 s		300	
Mounting torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m


Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting $T_J = 25^\circ\text{C}$, $L = 4.5$ mH, $R_G = 25\ \Omega$, $I_{AS} = 11$ A (see fig. 12)
- $I_{SD} \leq 11$ A, $dI/dt \leq 140$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$
- 1.6 mm from case



THERMAL RESISTANCE				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.75	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ °C}$	-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.6\text{ A}^b$	-	-	0.52	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 6.6\text{ A}$	6.1	-	-	S
Dynamic						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$	-	1423	-	pF
Output capacitance	C_{oss}		-	208	-	
Reverse transfer capacitance	C_{rss}		-	8.1	-	
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	2000	-
			$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	55	-
Effective output capacitance	$C_{oss\text{ eff.}}$	$V_{DS} = 0\text{ V to } 400\text{ V}$	-	97	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b	-	-	52	nC
Gate-source charge	Q_{gs}		-	-	13	
Gate-drain charge	Q_{gd}		-	-	18	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 11\text{ A}, R_G = 9.1\text{ }\Omega, R_D = 22\text{ }\Omega, \text{ see fig. 10}^b$	-	14	-	ns
Rise time	t_r		-	35	-	
Turn-off delay time	$t_{d(off)}$		-	32	-	
Fall time	t_f		-	28	-	
Gate input resistance	R_g	$f = 1\text{ MHz}, \text{ open drain}$	0.5	-	3.2	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	11	A
Pulsed diode forward current ^a	I_{SM}		-	-	44	
Body diode voltage	V_{SD}	$T_J = 25\text{ °C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ °C}, I_F = 11\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	510	770	ns
Body diode reverse recovery charge	Q_{rr}		-	3.4	5.1	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
- c. $C_{oss\text{ eff.}}$ effective is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

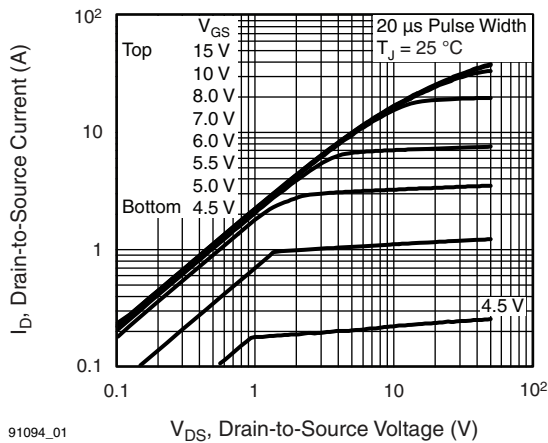


Fig. 1 - Typical Output Characteristics

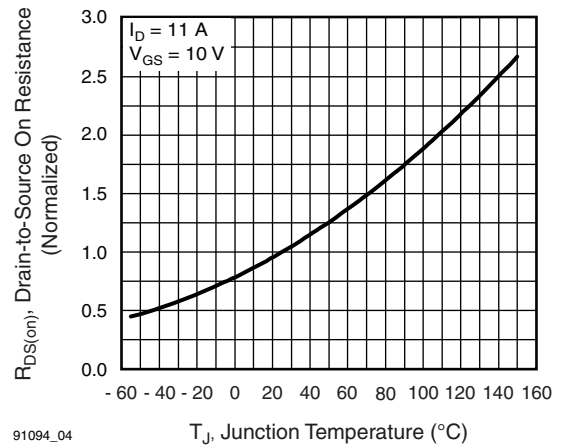


Fig. 4 - Normalized On-Resistance vs. Temperature

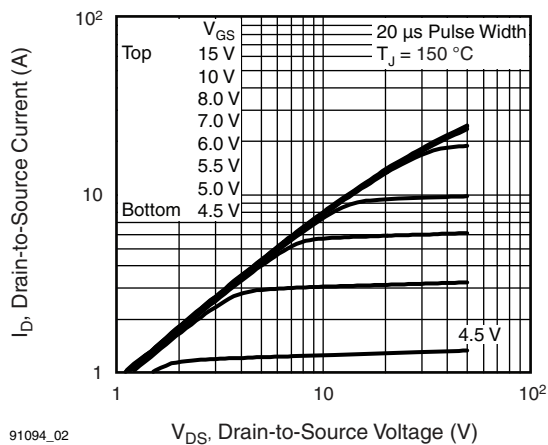


Fig. 2 - Typical Output Characteristics

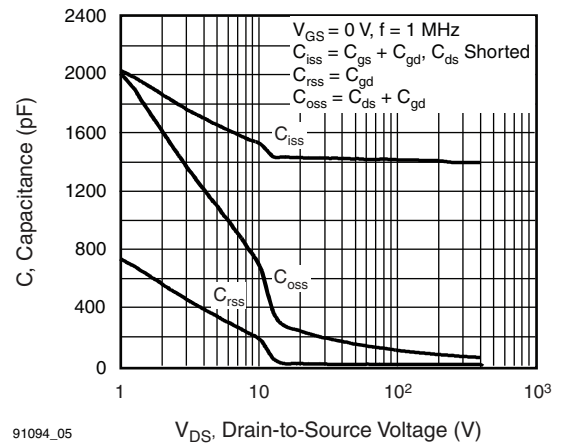


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

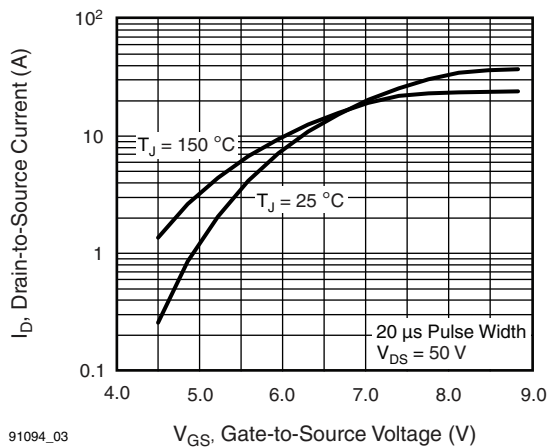


Fig. 3 - Typical Transfer Characteristics

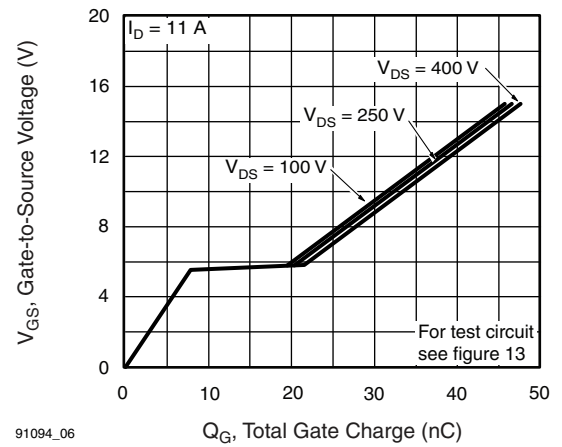


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

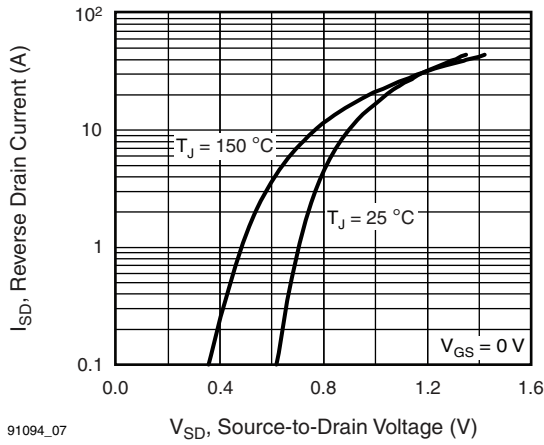


Fig. 7 - Typical Source-Drain Diode Forward Voltage

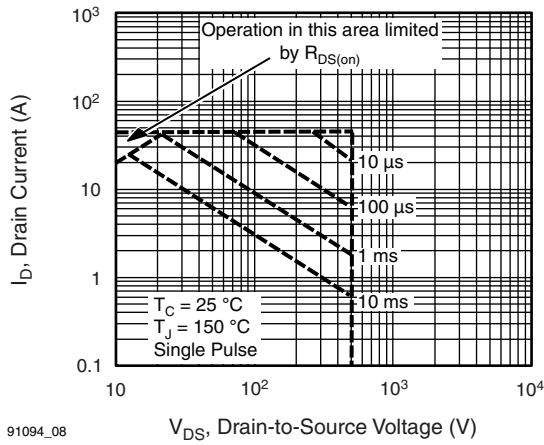


Fig. 8 - Maximum Safe Operating Area

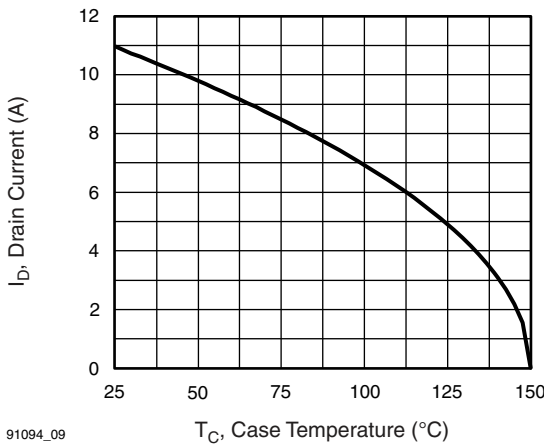


Fig. 9 - Maximum Drain Current vs. Case Temperature

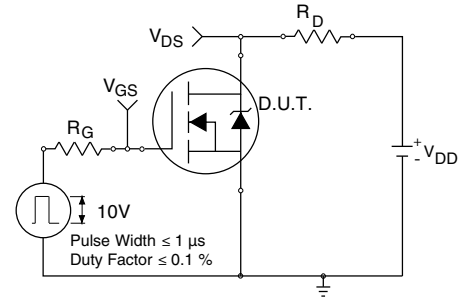


Fig. 10a - Switching Time Test Circuit

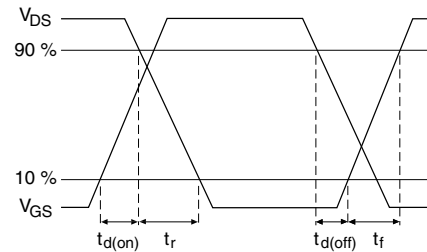


Fig. 10b - Switching Time Waveforms

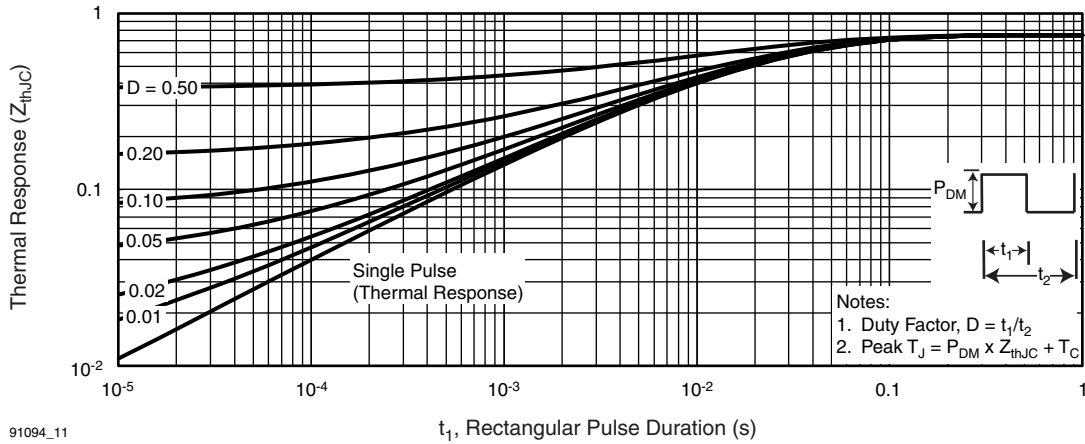


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

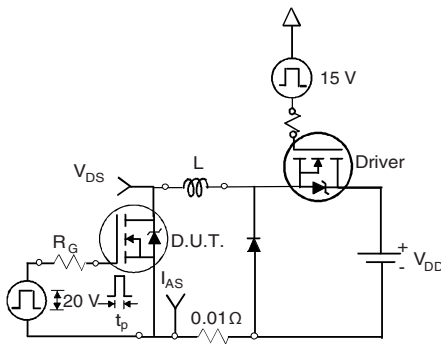


Fig. 12a - Unclamped Inductive Test Circuit

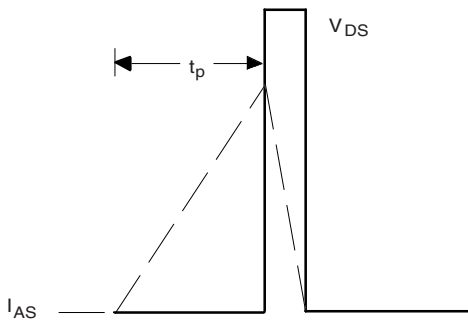


Fig. 12b - Unclamped Inductive Waveforms

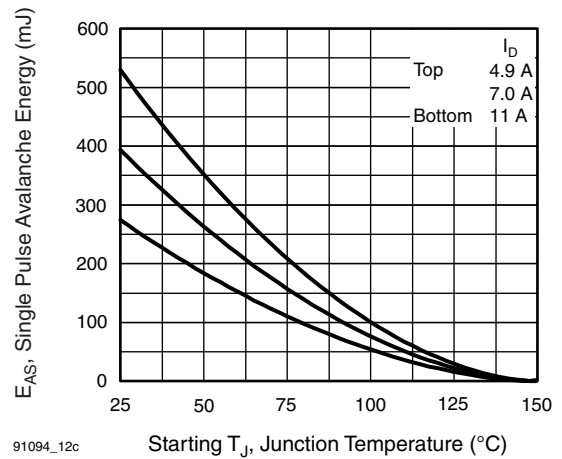


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

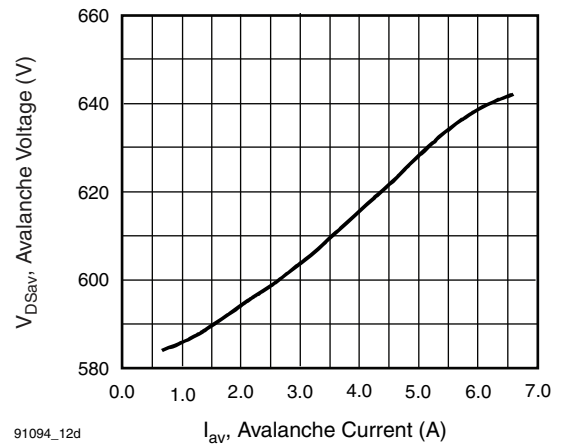


Fig. 12d - Typical Drain-to-Source Voltage vs. Avalanche Current

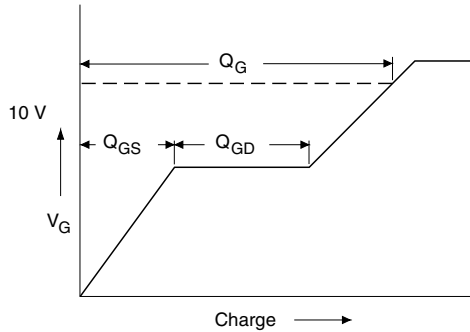


Fig. 13a - Basic Gate Charge Waveform

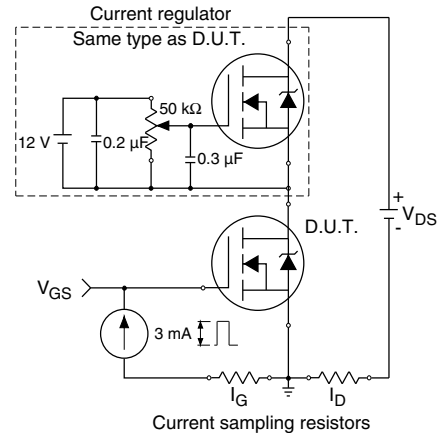


Fig. 13b - Gate Charge Test Circuit

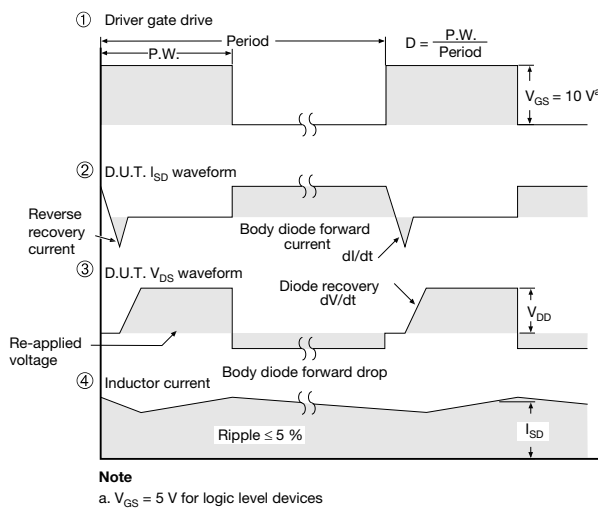
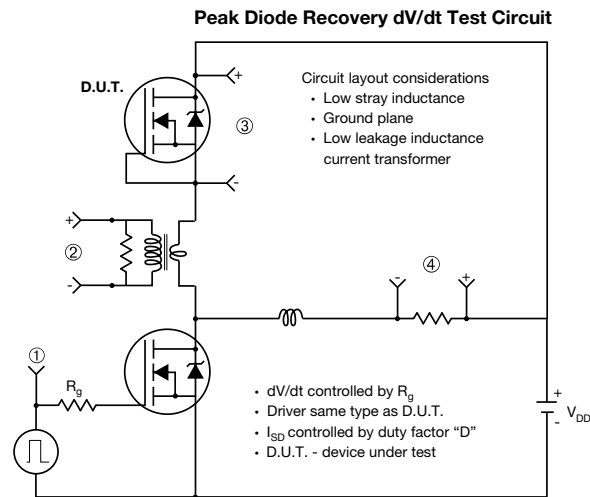


Fig. 14 - For N-Channel

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